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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/666,865	09/18/2003	Min-Su Kim	5484-110	8456	
20575	7590 12/30/2005		EXAM	EXAMINER	
MARGER JOHNSON & MCCOLLOM, P.C. 210 SW MORRISON STREET, SUITE 400			DOLAN, JE	DOLAN, JENNIFER M	
PORTLAND,	•	+00	ART UNIT	PAPER NUMBER	
			2813		
			DATE MAILED: 12/30/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
5	Advisory Action	10/666,865	KIM, MIN-SU				
	Before the Filing of an Appeal Brief	Examiner	Art Unit				
		Jennifer M. Dolan	2813				
	The MAILING DATE of this communication appe	ears on the cover sheet with the o	correspondence add	ress			
THE			-				
1. 🗌	HE REPLY FILED 02 December 2005 FAILS TO PLACE THIS APPLICATION IN CONDITION FOR ALLOWANCE. The reply was filed after a final rejection, but prior to or on the same day as filing a Notice of Appeal. To avoid abandonment of this application, applicant must timely file one of the following replies: (1) an amendment, affidavit, or other evidence, which places the application in condition for allowance; (2) a Notice of Appeal (with appeal fee) in compliance with 37 CFR 41.31; or (3) a Request for Continued Examination (RCE) in compliance with 37 CFR 1.114. The reply must be filed within one of the following time periods:						
	The period for reply expiresmonths from the mailing. The period for reply expires on: (1) the mailing date of this A no event, however, will the statutory period for reply expire I Examiner Note: If box 1 is checked, check either box (a) or TWO MONTHS OF THE FINAL REJECTION. See MPEP 7	Advisory Action, or (2) the date set forth ater than SIX MONTHS from the mailing (b). ONLY CHECK BOX (b) WHEN THE	g date of the final rejecti	on.			
Extensions of time may be obtained under 37 CFR 1.136(a). The date on which the petition under 37 CFR 1.136(a) and the appropriate extension fee have been filed is the date for purposes of determining the period of extension and the corresponding amount of the fee. The appropriate extension fee under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the shortened statutory period for reply originally set in the final Office action; or (2) as set forth in (b) above, if checked. Any reply received by the Office later than three months after the mailing date of the final rejection, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). NOTICE OF APPEAL							
2. The Notice of Appeal was filed on A brief in compliance with 37 CFR 41.37 must be filed within two months of the date of filing the Notice of Appeal (37 CFR 41.37(a)), or any extension thereof (37 CFR 41.37(e)), to avoid dismissal of the appeal. Since a Notice of Appeal has been filed, any reply must be filed within the time period set forth in 37 CFR 41.37(a). AMENDMENTS							
3. 🗀	The proposed amendment(s) filed after a final rejection, (a) They raise new issues that would require further co (b) They raise the issue of new matter (see NOTE belo (c) They are not deemed to place the application in be appeal; and/or (d) They present additional claims without canceling a NOTE: (See 37 CFR 1.116 and 41.33(a)).	nsideration and/or search (see NO bw); tter form for appeal by materially re corresponding number of finally rej	TE below); ducing or simplifying				
	The amendments are not in compliance with 37 CFR 1.1 Applicant's reply has overcome the following rejection(s)	21. See attached Notice of Non-Co	empliant Amendment	(PTOL-324).			
	Newly proposed or amended claim(s) would be a non-allowable claim(s).	· 	timely filed amendme	ent canceling the			
	For purposes of appeal, the proposed amendment(s): a) how the new or amended claims would be rejected is pro The status of the claim(s) is (or will be) as follows: Claim(s) allowed: Claim(s) objected to: Claim(s) rejected: Claim(s) withdrawn from consideration: DAVIT OR OTHER EVIDENCE	☐ will not be entered, or b) ☐ wi vided below or appended.	ll be entered and an e	explanation of			
8. 🗌	The affidavit or other evidence filed after a final action, be because applicant failed to provide a showing of good an was not earlier presented. See 37 CFR 1.116(e).	d sufficient reasons why the affiday	vit or other evidence is	s necessary and			
10. [The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to one showing a good and sufficient reasons why it is necessar. The affidavit or other evidence is entered. An explanation uest for Reconsideration/other	overcome <u>all</u> rejections under appe y and was not earlier presented. S	al and/or appellant fai ee 37 CFR 41.33(d)(ils to provide a 1).			
	The request for reconsideration has been considered bu See Continuation Sheet.			nce because:			
	Note the attached Information Disclosure Statement(s). Other:	· 177	NO(S). Sylvanical Arl Whitehead, Jr.	4			
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Continuation of 11, does NOT place the application in condition for allowance because:

The Applicant first argues that the finality of the last office action was not proper. The Examiner disagrees, and points out that the newly applied rejections and references in the last office action were specifically applied to provide the newly claimed limitation that the insulation layer is disposed in contact with a sidewall of the gate line. As this limitation is substantially different from the previous claimed subject matter, in which the insulation layer merely needed to cover the gate line, the addition of a new reference to teach this newly claimed element is considered "necessitated by amendment."

The Applicant further argues that the SOI layers are located entirely in the active region, and no part of the SOI is disposed in the device isolation area. Hence, "it is incorrect to interpret Assaderaghi's shallow trench isolation regions as being included in, or part of, the SOI layer." This is not persuasive, because Assaderaghi clearly shows the STI regions disposed within the exact same layer as the SOI regions. Hence, it would be considered normal and proper to state that the STI regions are formed in the SOI layer. Assaderaghi additionally indicates that the SOI substrate is provided, and then STI structures are provided in that SOI layer, preferably with the bottom of the STI extending to the top of the buried oxide layer (see column 5, lines 43-62). Furthermore, it is not particularly relevant whether the STI structures of Assaderaghi are considered to be inside the SOI layer, since Assaderaghi, when combined with Chen, provides a structure in which a portion of the SOI layer remains underneath the isolation structure.

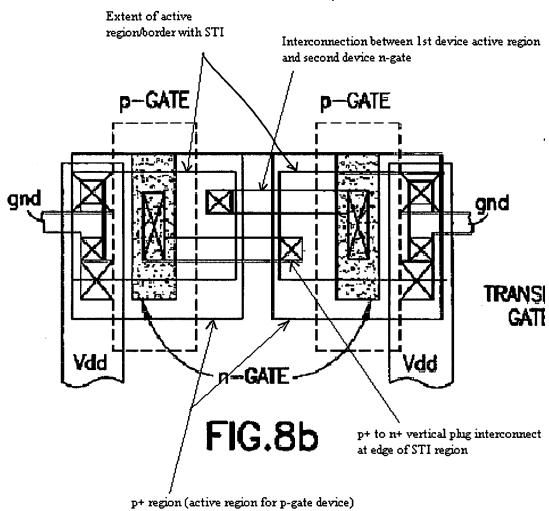
The Applicant further argues that the Applicant's specification and drawings illustrate a continuous SOI region, whereas Assaderaghi does not. The Examiner does not see the relevance of this issue, as such a feature is not specifically claimed, and is additionally present in the combination of Assaderaghi and Chen applied against claim 1.

The Applicant even further argues that the "left-most" n gate of fig. 8b is not disposed over the oxide isolation portion, and that it is not apparent in figure 8b where the active region is located. This is not persuasive, because the term "over" only requires that the feature be at a level higher than the active area and STI, rather than requiring any sort of overlap between the features. Furthermore, figure 7b directly shows and overlap between the n-gate and the active region. Similarly, since figures 7b and 8b show side and top views of the same area, it is apparent that the STI region includes an area directly under part of the n-gate (see attached figures).

The Applicant argues that the insulation layer in Assaderaghi is not contacting an upper surface of the active layer, but rather is disposed on top of the gate insulation layer. This is not persuasive, because Assaderaghi shows that the gate oxide layer is only present directly under the gate and the gate sidewalls (see figures 2, 3, 7). Hence, the isolation film contacts the upper surface of the source and drain regions, which are part of the active layer.

The Applicant further argues that Assaderaghi does not indicate that the stud interconnection 212 that rises vertically from the second gate line is part of the same interconnect structure as the stud interconnection 212 that rises vertically from the active region surrounding the first gate line. This is not persuasive, because figure 8b, which is the top view of the device of figure 7b, directly shows electrical connection between the second gate line and the first active region, as is stated in the previous office action.

The Applicant even further argues that there is no evidence in Assaderaghi that an LDD structure is present, such that the motivations for combining with Hills would apply. The Examiner disagrees, since Assaderaghi shows dopant regions that have a shape characteristic of regions including LDD portions, and further, Assaderaghi explicitly states that the device may include LDD regions (see column 12, lines 62-67). The Applicant is further reminded that since the Applicant's specification does not expressly or implicitly provide any purpose for the absense of the sidewall spacers, then the prior art teachings that it is known in the art and permitted to omit such layers is sufficient motivation for rejection.



Correspondence between figure 7B and figure 8B features